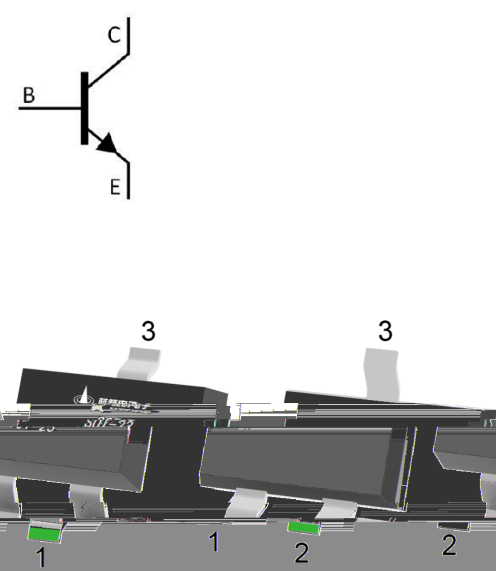


Rev.J May.-2023

SOT-23 NPN Silicon NPN transistor in a SOT-23 Plastic Package.

S8550M
Complementary pair with S8550M,HF Product.

Power amplifier applications.

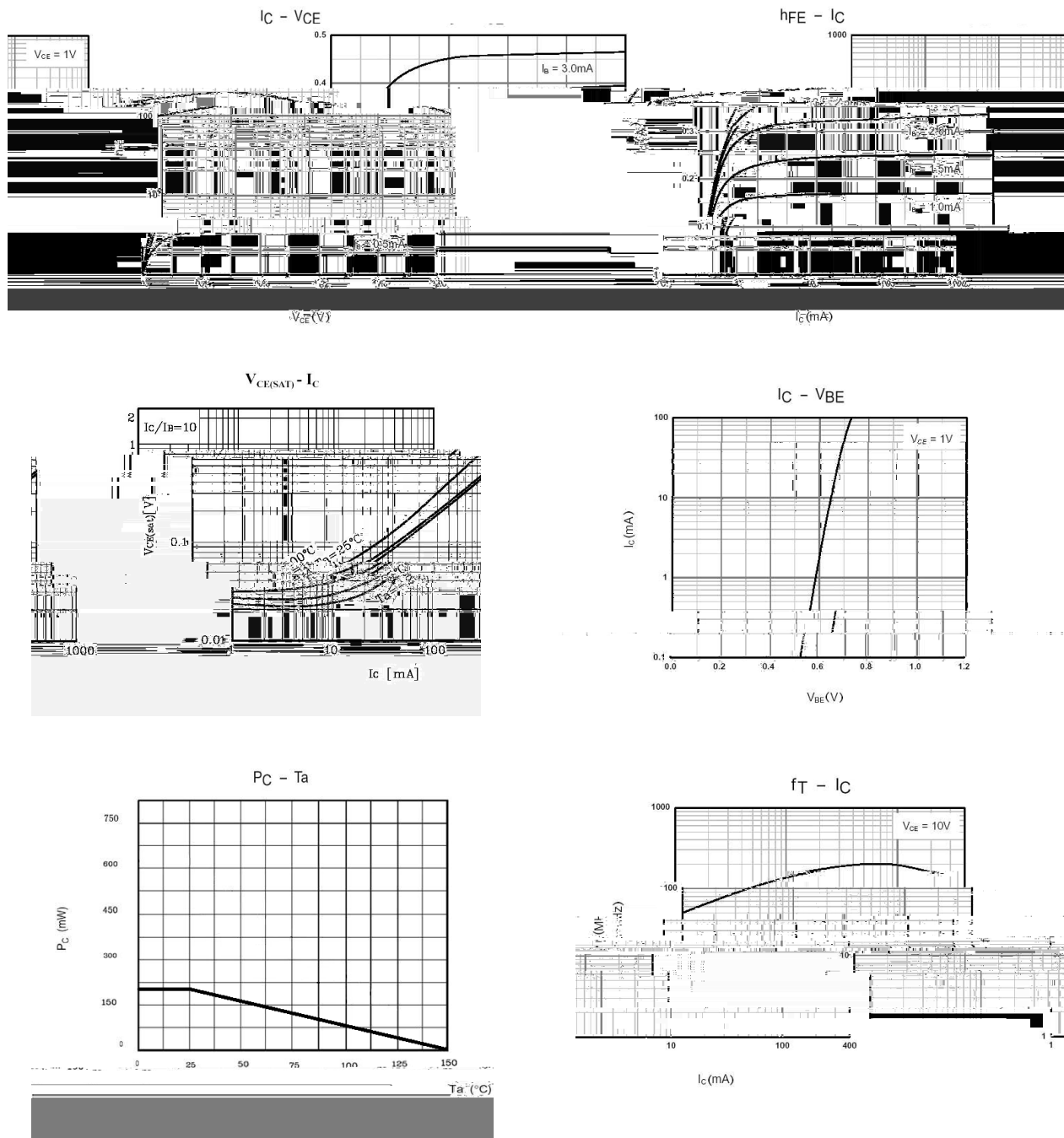


PIN1 Base PIN 2 Emitter PIN 3 Collector

h _{FE} Classifications			
Symbol	B	C	D
h _{FE} Range	100~1000	100~1000	100~1000

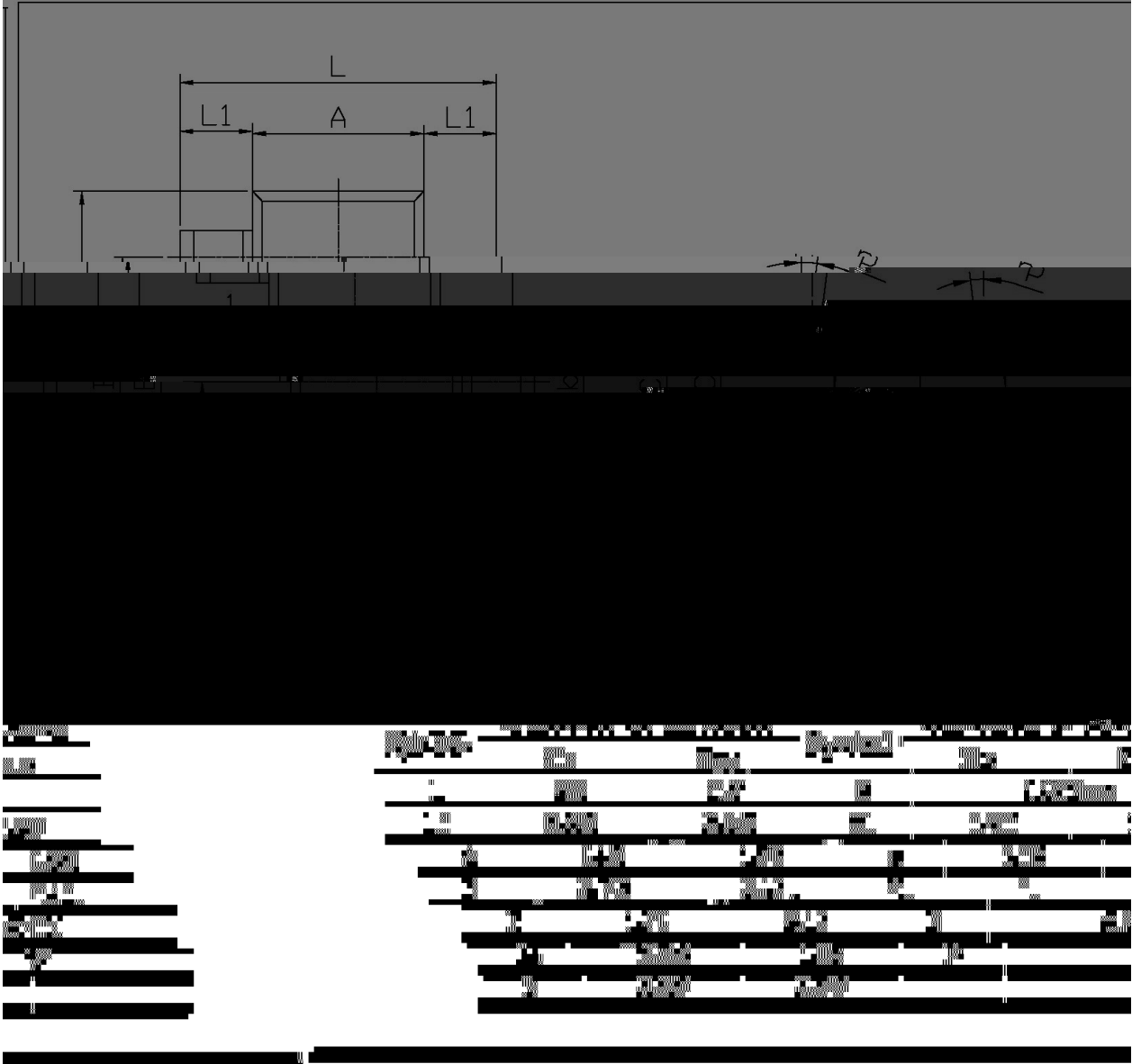
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	25	V
Emitter to Base Voltage	V_{EBO}	6.0	V
Collector Current	I_C	800	mA
Base Current	I_B	200	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

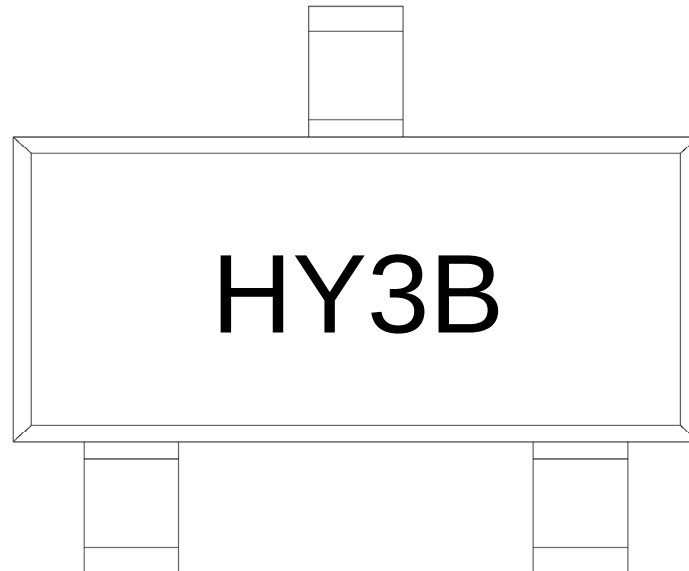
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=0.1mA$ $I_E=0$	40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=2.0mA$ $I_B=0$	25			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=0.1mA$ $I_C=0$	6.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=35V$ $I_E=0$			0.1	A
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=6.0V$ $I_C=0$			0.1	A
DC Current Gain	$h_{FE(1)}$	$V_{CE}=1.0V$ $I_C=100mA$	85		300	
	$h_{FE(2)}$	$V_{CE}=1.0V$ $I_C=500mA$	40			
	$h_{FE(3)}$	$V_{CE}=1.0V$ $I_C=5.0mA$	45			
Collector-Emitter Saturation voltage	$V_{CE(sat)}$	$I_C=500mA$ $I_B=50mA$		0.28	0.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=500mA$ $I_B=50mA$		0.98	1.2	V
Base-Emitter Voltage	V_{BE}	$V_{CE}=1.0V$ $I_C=10mA$		0.66	1.0	V
Transition Frequency	f_T	$V_{CE}=10V$ $I_C=50mA$	100	190		MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10V$ $I_E=0$ $f=1.0MHz$		9.0		pF



SMT-23

单位: mm





H

Y3

B h_{FE}

Note:

H Company Code

Y3 Product Type Code

B h_{FE} Classifications Symbol Code

